UNIKC Semiconductor

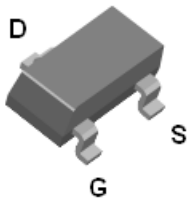
RoHS Compliant

P2803BMG

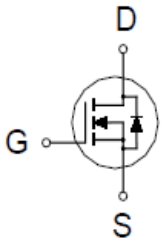
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	28mΩ @V_{GS} = 10V	6A



SOT-23



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A = 25 °C	I_D	6	A
	T_A = 70 °C		4	
Pulsed Drain Current[1]		I_{DM}	30	
Avalanche Current		I_{AS}	21	
Avalanche Energy	L = 0.1mH	E_{AS}	22	mJ
Power Dissipation	T_A = 25 °C	P_D	1	W
	T_A = 70 °C		0.6	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient(Steady-State)	$R_{\theta JA}$		125	°C / W

[1]Pulse width limited by maximum junction temperature.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.8	3.0	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V			1	μA
		V_{DS} = 20V, V_{GS} = 0V , T_J = 125 °C			10	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 10V, V_{GS} = 10V	30			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 4A		35	40	mΩ
		V_{GS} = 10V, I_D = 6A		24	28	
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 6A		9		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		482		pF
Output Capacitance	C_{oss}			165		
Reverse Transfer Capacitance	C_{rss}			104		
Total Gate Charge[2]	$Q_{g(VGS = 10V)}$	V_{DS} = 0.5$V_{(BR)DSS}$, I_D = 6A		9.5		nC
	$Q_{g(VGS = 4.5V)}$			4.5		
Gate-Source Charge[2]	Q_{gs}			2.4		
Gate-Drain Charge[2]	Q_{gd}			2		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = 15V, I_D ≅ 6A V_{GS} = 10V, R_{GS} = 3Ω		5		nS
Rise Time[2]	t_r			7		
Turn-Off Delay Time[2]	$t_{d(off)}$			30		
Fall Time[2]	t_f			6		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICE (T_J = 25 ˚C)						
Continuous Current	I_S				0.8	A
Forward Voltage[1]	V_{SD}	I_F = 6A, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	I_F = 6A, dI_F/dt = 100 A/μs		20		nS
Reverse Recovery Charge	Q_{rr}			12		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

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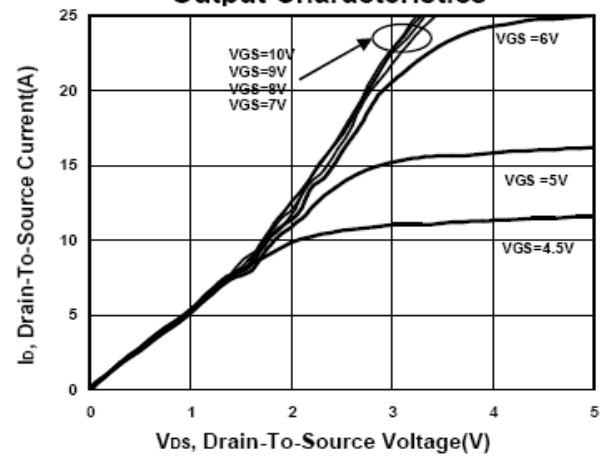
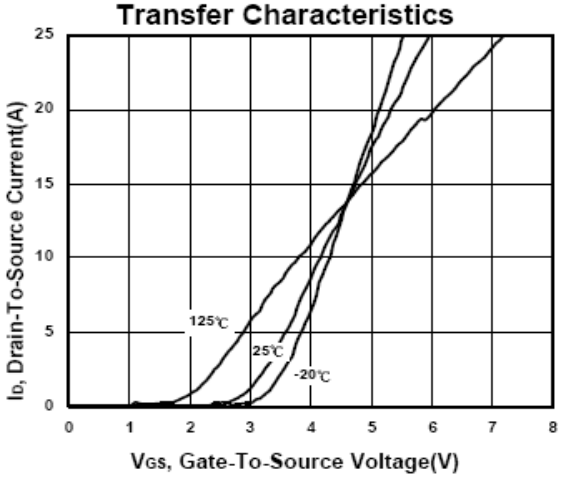
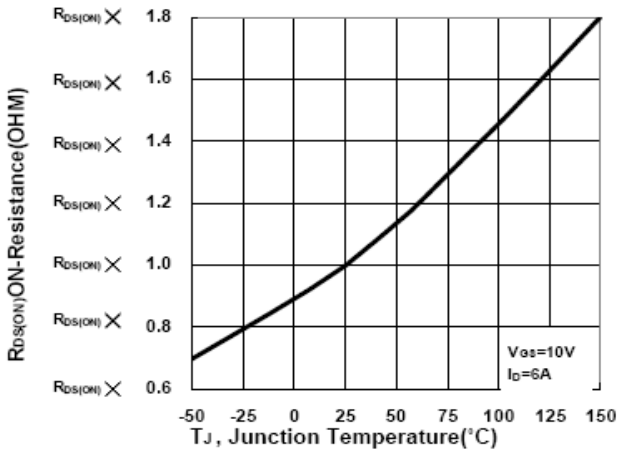
Output Characteristics



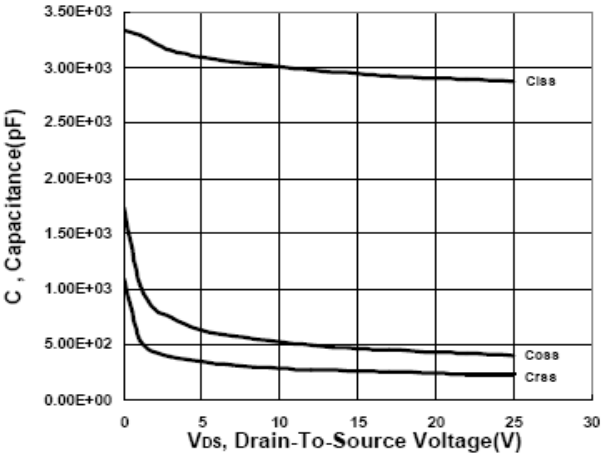
Transfer Characteristics



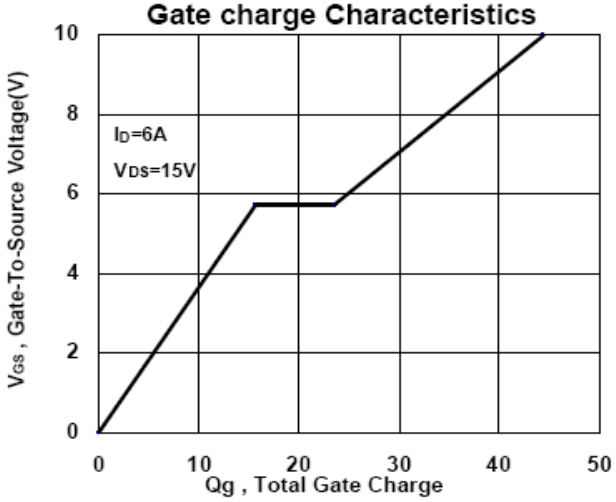
On-Resistance VS Temperature



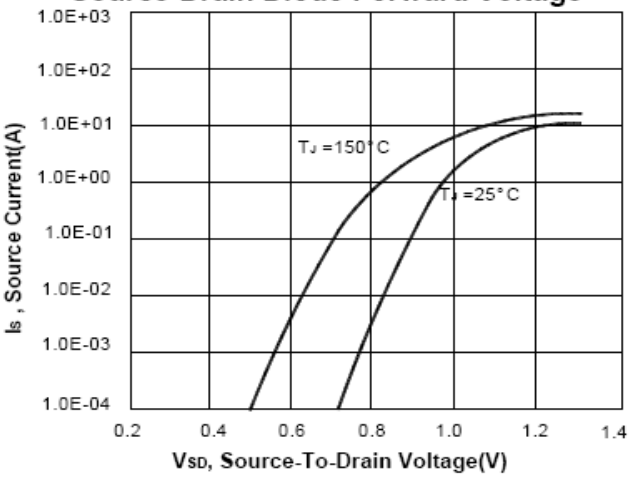
Capacitance Characteristic



Gate charge Characteristics



Source-Drain Diode Forward Voltage



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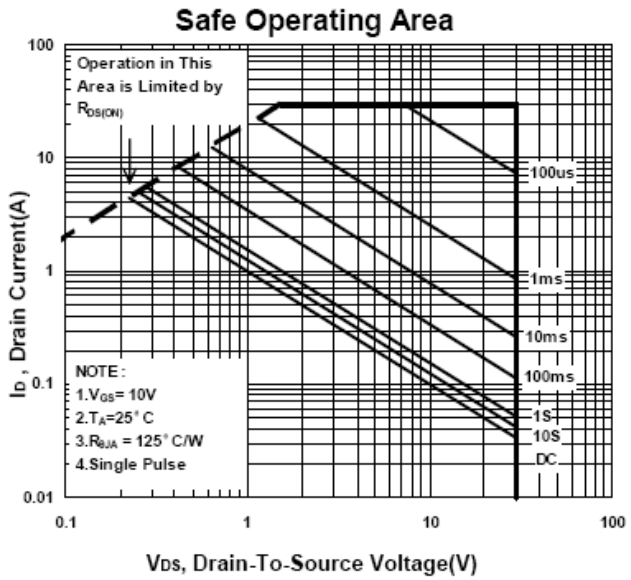

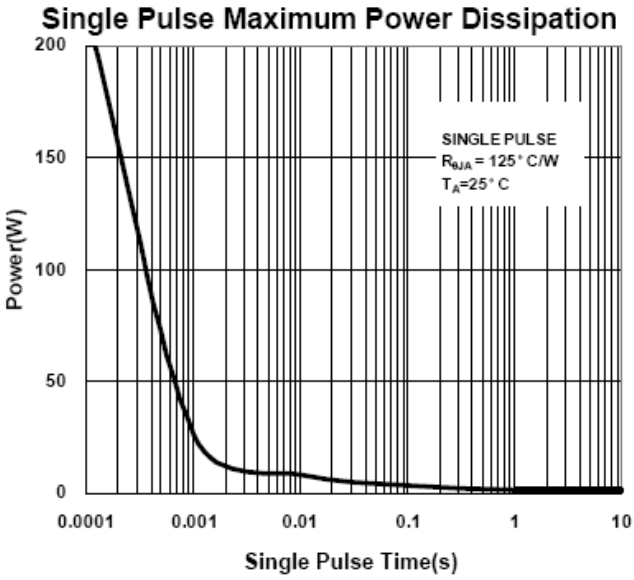

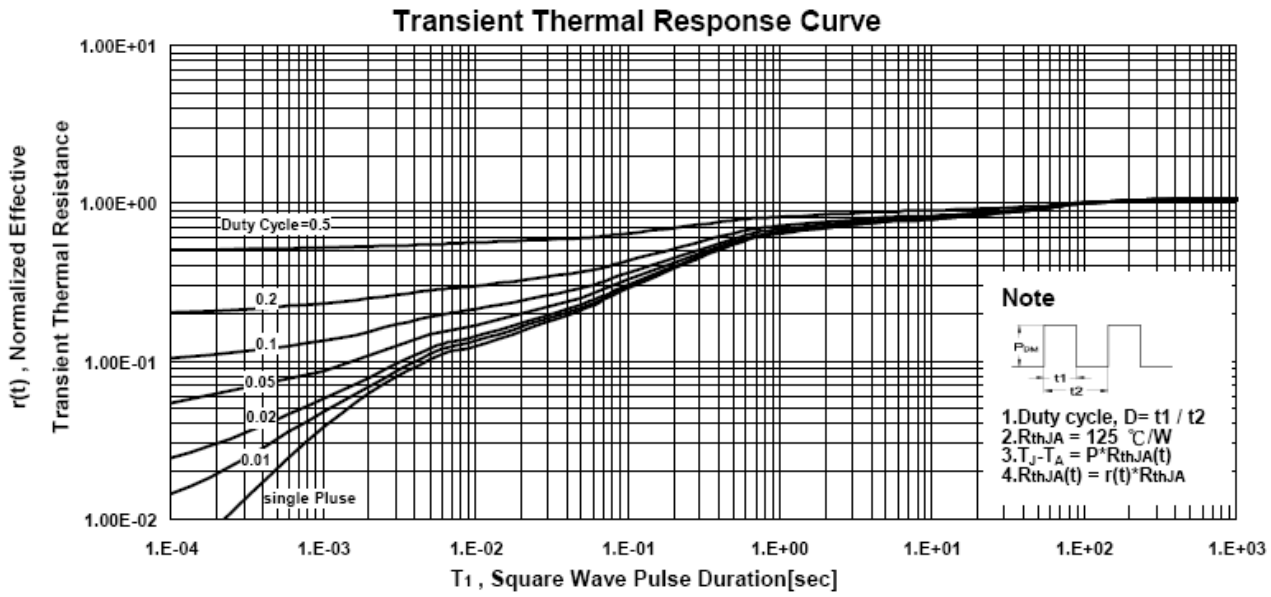

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Package Dimension

SOT-23-3 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A		1.05		H	0.1		0.2
B	2.4		3	I	0.3		0.6
C	1.4		1.73				
D	2.7		3.1				
E	1		1.31				
F	0		0.15				
G	0.3		0.5